

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in this application.

Listing of Claims:

Claim 1 (Currently Amended): A semiconductor light emitting element having a resonator composed of paired multi-layer reflecting films disposed at a constant distance on a GaAs substrate and having a light emitting layer disposed at a loop position of a standing wave in the resonator, wherein a multi-layer reflecting film on the GaAs substrate side of the light emitting layer comprises ~~is composed of~~ plural layers of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$) and a multi-layer reflecting film on the other side of the light emitting layer comprises ~~is composed of~~ plural layers of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1, 0 \leq z \leq 1$).

Claim 2 (Currently Amended): A semiconductor light emitting element as defined in claim 1, wherein the light emitting layer comprises ~~is composed of~~ a single- or multi-layer film of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1, 0 \leq z \leq 1$).

Claim 3 (Previously Presented): A semiconductor light emitting element as defined in claim 1 or 2, wherein a current constricting structure of an insulation layer is disposed above the light emitting layer.

Claim 4 (Currently Amended): A semiconductor light emitting element as defined in claim 11 3, wherein the current constricting structure is formed by a layer of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$).

Claim 5 (Currently Amended): A semiconductor light emitting element as defined in claim 11 3, wherein the current constricting structure is formed by a layer of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1, 0 \leq z \leq 1$).

Claim 6 (Canceled)

Claim 7 (Currently Amended): A semiconductor light emitting element as defined in claim 4 3, wherein a the current diffusion layer is formed by a layer of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$).

Claim 8 (Canceled).

Claim 9 (Currently Amended): A semiconductor light emitting element as defined in claim 12 3, wherein the current diffusion layer is formed by a transparent electrode having the transmittance of the emitted light, which transmittance is not less than 50%.

Claim 10 (Previously Presented) A semiconductor light emitting element as defined in claim 1, wherein the GaAs substrate has a surface inclined at an angle of not less than 2 degrees in the direction $[0\ 1\ 1]$ or $[0\ -1\ -1]$ from the plane $(1\ 0\ 0)$.

Claim 11 (Currently Amended): A semiconductor light emitting element as defined in claim 1 or 2, wherein a current constricting structure of the same conductive type material as the GaAs substrate is disposed above the light emitting layer.

Claim 12 (Previously Presented): A semiconductor light emitting element as defined in claim 11, wherein a current diffusion layer is formed above the layer forming the current constricting structure.

Claim 13 (Previously Presented): A semiconductor light emitting element as defined in claim 12, wherein the current diffusion layer is formed by a layer of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

Claim 14 (Previously Presented): A semiconductor light emitting element as defined in claim 4, wherein a current diffusion layer is formed above the layer forming the current constricting structure.

Claim 15 (Previously Presented): A semiconductor light emitting element as defined in claim 14, wherein the current diffusion layer is formed by a layer of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

Claim 16 (Previously Presented): A semiconductor light emitting element as defined in claim 5, wherein a current diffusion layer is formed above the layer forming the current constricting structure.

Claim 17 (Previously Presented): A semiconductor light emitting element as defined in claim 16, wherein the current diffusion layer is formed by a layer of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

Claim 18 (Currently Amended): A semiconductor light emitting element, comprising:
a substrate;
a light emitting layer; and
a resonator comprising first and second reflecting films disposed on opposite sides of the light emitting layer, wherein the first reflecting film comprises $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$) and the second reflecting film comprises $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$),
wherein the first reflecting film is disposed on the same side of the light emitting layer as the substrate.

Claim 19 (Previously Presented): A semiconductor light emitting element as defined in claim 18, wherein the light emitting layer comprises one or more films of $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

Claim 20 (Previously Presented): A semiconductor light emitting element as defined in claim 18, further comprising:

a current constricting layer provided on the side of the light emitting layer opposite the side on which the substrate is provided.

Claim 21 (Withdrawn): A semiconductor light emitting element as defined in claim 20, wherein the current constricting layer comprises an insulating layer.

Claim 22 (Currently Amended): A semiconductor light emitting element as defined in claim 20, wherein the current constricting layer comprises ~~the same~~ material of the same conductive type as the substrate.

Claim 23 (Previously Presented): A semiconductor light emitting element as defined in claim 20, further comprising:

a current diffusion layer formed on the current constricting layer.

Claim 24 (Previously Presented): A semiconductor light emitting element as defined in claim 23, wherein the current diffusion layer comprises $\text{Al}_y\text{Ga}_z\text{In}_{1-y-z}\text{P}$ ($0 \leq y \leq 1$, $0 \leq z \leq 1$).

Claim 25 (Previously Presented): A semiconductor light emitting element as defined in claim 18, wherein the substrate comprises a GaAs substrate having a surface inclined at not less than 2 degrees in the direction $[0\ 1\ 1]$ or $[0\ -1\ -1]$ from the plane $(1\ 0\ 0)$.

Claim 26 (Withdrawn): A semiconductor light emitting element as defined in claim 18, wherein the resonator has a resonant wavelength of 650 nm.

Claim 27 (Previously Presented): A semiconductor light emitting element as defined in claim 18, wherein the length of the resonator is 1.5 times the resonant wavelength of the resonator.

Claim 28 (Canceled).

Claim 29 (New) A semiconductor light emitting element as defined in claim 5,
wherein a current diffusion layer is formed by a layer of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$).

Claim 30 (New): A semiconductor light emitting element as defined in claim 3,
wherein a current diffusion layer is formed above the layer forming the current constricting
structure.

Claim 31 (New): A semiconductor light emitting element as defined in claim 30,
wherein the current diffusion layer is formed by a transparent electrode having the transmittance
of the emitted light, which transmittance is not less than 50%.

Claim 32 (New): A semiconductor light emitting element as defined in claim 12,
wherein the current diffusion layer is formed by a layer of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ ($0 \leq x \leq 1$).